TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

## HN1B26FS

#### General-Purpose Amplifier Applications

Unit: mm

Q1

· High voltage and high current

:  $V_{CEO} = 50 \text{ V}$ ,  $I_{C} = 100 \text{ mA (max)}$ 

• Excellent h<sub>FE</sub> linearity : h<sub>FE</sub> ( $I_C = 0.1 \text{ mA}$ )/h<sub>FE</sub> ( $I_C = 2 \text{ mA}$ ) = 0.95 (typ.)

• High h<sub>FE</sub> : h<sub>FE</sub> = 120~400

Q2

· High voltage and high current

:  $V_{CEO} = -50 \text{ V}$ ,  $I_{C} = -100 \text{ mA (max)}$ 

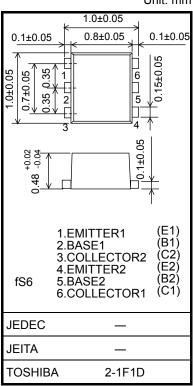
• Excellent hFF linearity :

 $h_{FE} (I_C = -0.1 \text{ mA})/h_{FE} (I_C = -2 \text{ mA}) = -0.95 \text{ (typ.)}$ 

• High h<sub>FE</sub> : h<sub>FE</sub> = 120~400

### Q1 Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	60	V
Collector-emitter voltage	V <sub>CEO</sub>	50	٧
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	IC	100	mA
Base current	Ι <sub>Β</sub>	30	mA



Weight: 0.0008 g (typ.)

#### Q2 Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	IC	-100	mA
Base current	Ι <sub>Β</sub>	-30	mA

#### Q1, Q2 Common Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector power dissipation	PC	50*	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

<sup>\*:</sup> Total rating

## Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = 60 V, I <sub>E</sub> = 0	_	_	0.1	μА
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	_	_	0.1	μΑ
DC current gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 2 mA	120	_	400	_
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA	_	0.1	0.25	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 1 mA	60	_	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	0.95		pF

## Q2 Electrical Characteristics (Ta = 25°C)

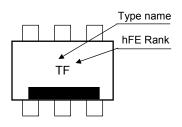
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-0.1	μА
Emitter cutoff current	I <sub>EBO</sub>	$V_{EB} = -5 \text{ V}, I_C = 0$	_	_	-0.1	μА
DC current gain	h <sub>FE</sub> (Note)	$V_{CE} = -6 \text{ V}, I_{C} = -2 \text{ mA}$	120	_	400	_
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$	_	-0.18	-0.3	V
Transition frequency	f <sub>T</sub>	$V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ mA}$	80	_	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	-	1.6		pF

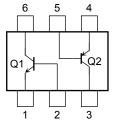
Note: hFE classification Y (F): 120~240, GR (H): 200~400

( ) marking symbol

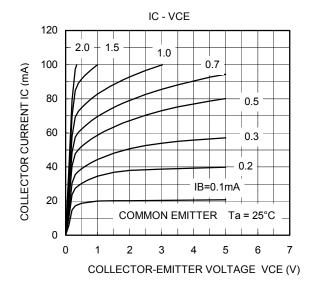
# Marking (top view)

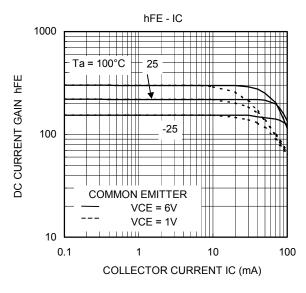
## **Equivalent Circuit**

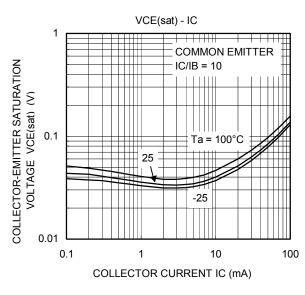


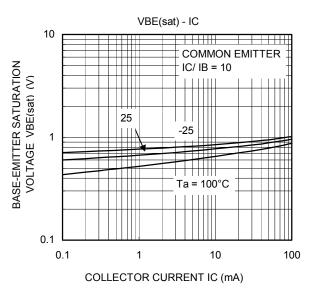


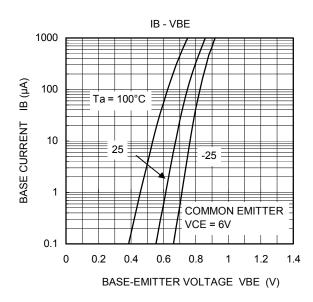
Q1





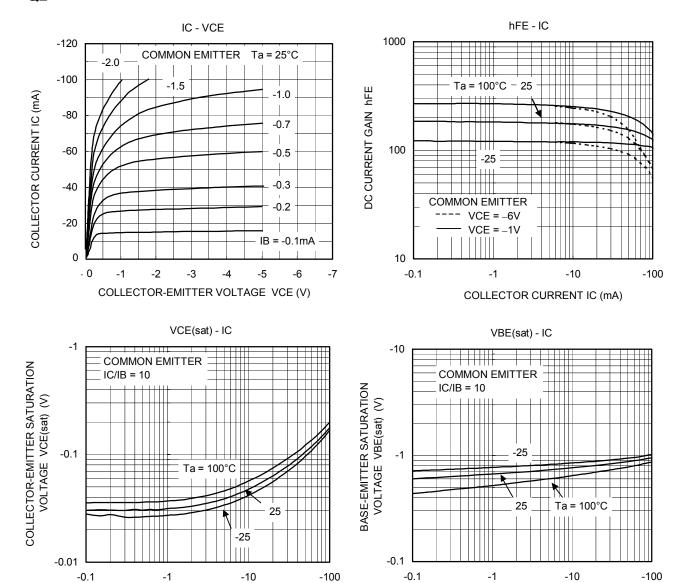


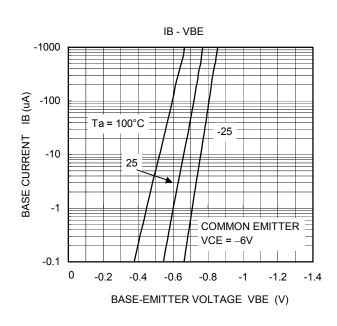




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Q2

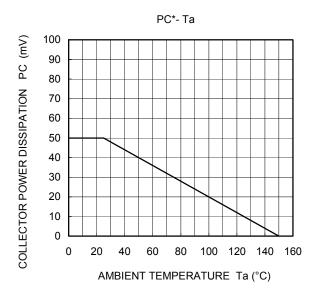




COLLECTOR CURRENT IC (mA)

COLLECTOR CURRENT IC (mA)

## Q1, Q2 COMMON



\*: Total rating

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20070701-EN GENERAL

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